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GR 98 P 1379 D

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By: Kanghong Chen

Date: June 27, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/885,553 Confirmation No. 6319
Applicant : Lars-Peter Heineck et al.
Filed : June 20, 2001
TC/A.U. : 2826
Examiner : Johannes P. Mondt
Title: : MOS Transistor in a Single-Transistor Memory Cell Having a Locally Thickened Gate Oxide

Docket No. : GR 98 P 1379 D
Customer No. : 24131

Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

S i r :

In response to the Office action dated February 25, 2005,
please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 4 of this paper.

An **Appendix** including the definitions of the terms "spacer" and "passivation layer" from the textbook "Technologie hochintegrierter Schaltungen" is attached following page 8 of this paper.